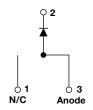


# HEXFRED® Ultrafast Soft Recovery Diode, 6 A



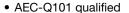
TO-263AB (D<sup>2</sup>PAK)



PRODUCT SUMMARY								
Package	TO-263AB (D <sup>2</sup> PAK)							
I <sub>F(AV)</sub>	6 A							
$V_{R}$	1200 V							
V <sub>F</sub> at I <sub>F</sub>	2.4 V							
t <sub>rr</sub> (typ.)	26 ns							
T <sub>J</sub> max.	150 °C							
Diode variation	Single die							

#### **FEATURES**

- Ultrafast and ultrasoft recovery
- Very low I<sub>RRM</sub> and Q<sub>rr</sub>
- · Specified at operating conditions
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C



 Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>





RoHS

HALOGEN FREE

#### **BENEFITS**

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- · Reduced parts count

#### **DESCRIPTION**

VS-HFA06TB120S is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 6 A continuous current, the VS-HFA06TB120S is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (IRRM) and does not exhibit any tendency to "snap-off" during the th portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA06TB120S is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Cathode to anode voltage	V <sub>R</sub>		1200	V					
Maximum continuous forward current	I <sub>F</sub>	T <sub>C</sub> = 100 °C	6						
Single pulse forward current	I <sub>FSM</sub>		80	Α					
Maximum repetitive forward current	I <sub>FRM</sub>		24						
Maximum naviar dissination	Б	T <sub>C</sub> = 25 °C	62.5	W					
Maximum power dissipation	P <sub>D</sub>	T <sub>C</sub> = 100 °C	25	VV					
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +150	°C					



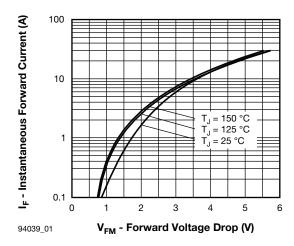


<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Cathode to anode breakdown voltage	$V_{BR}$	Ι <sub>R</sub> = 100 μΑ	1200	-	-				
Maximum forward voltage		I <sub>F</sub> = 6.0 A	-	2.7	3.0	V			
	V <sub>FM</sub>	I <sub>F</sub> = 12 A -		3.5	3.9				
		I <sub>F</sub> = 6.0 A, T <sub>J</sub> = 125 °C	-	2.4	2.8				
Maximum reverse	I <sub>RM</sub>	$V_R = V_R$ rated	-	0.26	5.0				
leakage current		T <sub>J</sub> = 125 °C, V <sub>R</sub> = 0.8 x V <sub>R</sub> rated	-	110	500	μA			
Junction capacitance	Ст	V <sub>R</sub> = 200 V	-	9.0	14	pF			
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body	=	8.0	-	nH			

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS			
Reverse recovery time	t <sub>rr</sub>	$I_F = 1.0 \text{ A}, dI_F/dt = 200$	$A/\mu s$ , $V_R = 30 V$	-	26	-	ns		
	t <sub>rr1</sub>	T <sub>J</sub> = 25 °C		-	53	80			
	t <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	87	130			
Peak recovery current	I <sub>RRM1</sub>	T <sub>J</sub> = 25 °C		-	4.4	8.0	- A - nC - A/μs		
reak recovery current	I <sub>RRM2</sub>	T <sub>J</sub> = 125 °C	$I_F = 6.0 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$	-	5.0	9.0			
Poverse receivery charge	Q <sub>rr1</sub>	T <sub>J</sub> = 25 °C	$V_R = 200 \text{ V}$	-	116	320			
Reverse recovery charge	Q <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	233	585			
Peak rate of recovery current during t <sub>b</sub>	dI <sub>(rec)M</sub> /dt1	T <sub>J</sub> = 25 °C		-	180	-			
	dI <sub>(rec)M</sub> /dt2	T <sub>J</sub> = 125 °C		-	100	- 1			

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Lead temperature	T <sub>lead</sub>	0.063" from case (1.6 mm) for 10 s	-	-	300	°C			
Thermal resistance, junction to case	R <sub>thJC</sub>		-	-	2.0				
Thermal resistance, junction to ambient	R <sub>thJA</sub>	Typical socket mount	-	-	80	K/W			
Thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth and greased	-	0.5	i				
Weight			-	2.0	-	g			
vveignt			-	0.07	-	oz.			
Marking device		Case style TO-263AB (D <sup>2</sup> PAK)		HFA06	ΓB120S				





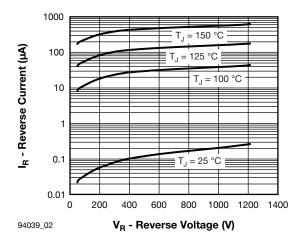


Fig. 1 - Typical Forward Voltage Drop Characteristics

Fig. 2 - Typical Reverse Current vs. Reverse Voltage

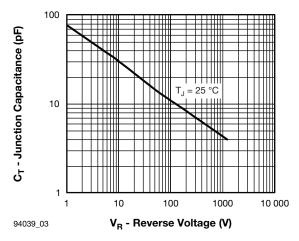


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

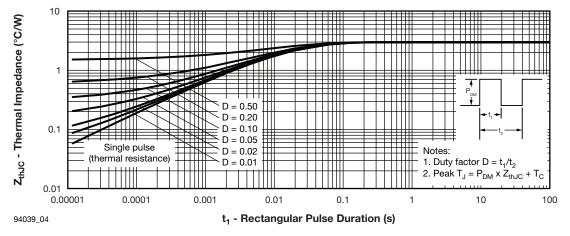


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics





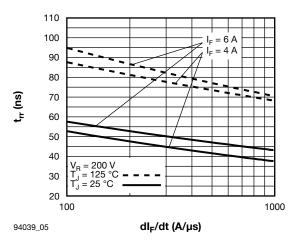


Fig. 5 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

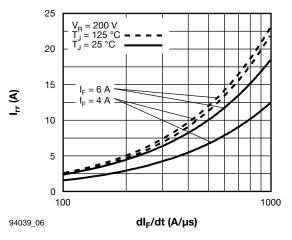


Fig. 6 - Typical Recovery Current vs. dl<sub>F</sub>/dt

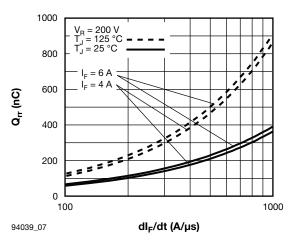


Fig. 7 - Typical Stored Charge vs. dl<sub>F</sub>/dt

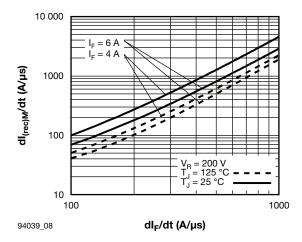


Fig. 8 - Typical  $dI_{(rec)M}/dt$  vs.  $dI_F/dt$ 

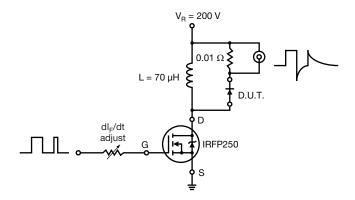
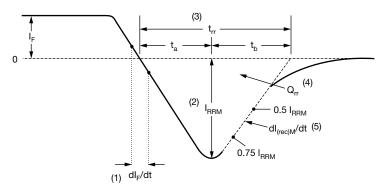


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dI<sub>F</sub>/dt rate of change of current through zero crossing
- (2) I<sub>RRM</sub> peak reverse recovery current
- (3)  $\rm t_{rr}$  reverse recovery time measured from zero crossing point of negative going  $\rm I_F$  to point where a line passing through 0.75  $\rm I_{RRM}$  and 0.50  $\rm I_{RRM}$  extrapolated to zero current.
- (4)  $Q_{rr}$  area under curve defined by  $t_{rr}$  and  $I_{RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

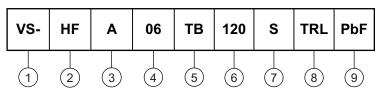
(5)  $dI_{(rec)M}/dt$  - peak rate of change of current during  $t_b$  portion of  $t_{rr}$ 

Fig. 10 - Reverse Recovery Waveform and Definitions



#### **ORDERING INFORMATION TABLE**

Device code



1 - Vishay Semiconductors product

2 - HEXFRED® family

Process designator: A = electron irradiated

4 - Current rating (06 = 6 A)

5 - Package outline (TB = TO-220, 2 leads)

Voltage rating (120 = 1200 V)

7 -  $S = D^2PAK$ 

None = tube

• TRL = tape and reel (left oriented)

• TRR = tape and reel (right oriented)

9 - • PbF = lead (Pb)-free

• P = lead (Pb)-free (for D<sup>2</sup>PAK TRR and TRL)

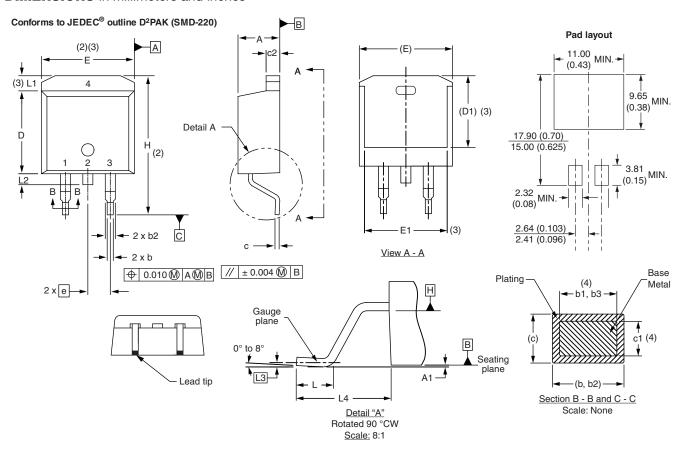
LINKS TO RELATED DOCUMENTS						
Dimensions <u>www.vishay.com/doc?95046</u>						
Part marking information	www.vishay.com/doc?95054					
Packaging information	www.vishay.com/doc?95032					

ORDERING INFORMATION (Example)									
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION						
VS-HFA06TB120SPBF	50	1000	Antistatic plastic tube						
VS-HFA06TB120STRRP	800	800	13" diameter reel						
VS-HFA06TB120STRLP	800	800	13" diameter reel						



### D<sup>2</sup>PAK

#### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIMETERS		INC	INCHES		NOTES	SYMBOL	MILLIM	ETERS	INC	HES	NOTES
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES		STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			Е	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

#### Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inch
- (7) Outline conforms to JEDEC® outline TO-263AB



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Vishay

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